

SN74LVC1G132 Single 2-Input NAND Gate With Schmitt-Trigger Inputs

1 Features

- Latch-up performance exceeds 100mA per JESD 78, Class II
- Available in Texas Instruments NanoStar™ and NanoFree™ packages
- Supports 5V V_{CC} operation
- Inputs accept voltages to 5.5V
- Maximum t_{pd} of 5.3ns at 3.3V
- Low power consumption, 10μA maximum I_{CC}
- ± 24 mA output drive at 3.3V
- I_{off} supports partial-power-down mode operation

2 Applications

- AV receiver
- Audio dock: portable
- Blu-ray player and home theater
- Embedded PC
- MP3 player/recorder (portable audio)
- Personal digital assistant (PDA)
- Power: telecom/server AC/DC supply: single controller: analog and digital
- Solid state drive (SSD): client and enterprise
- TV: LCD/digital and high-definition (HDTV)
- Tablet: enterprise
- Video analytics: server
- Wireless headset, keyboard, and mouse

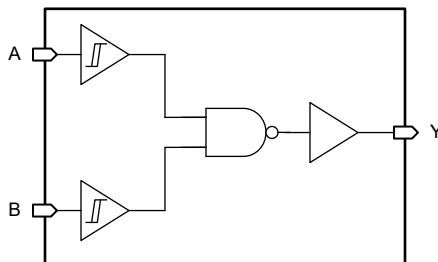
3 Description

The SN74LVC1G132 device is a single 2-input positive NAND gate with Schmitt-trigger inputs. This device performs the Boolean function $Y = \overline{A \cdot B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

Package Information

PART NUMBER	PACKAGE ⁽¹⁾	PACKAGE SIZE ⁽²⁾	BODY SIZE ⁽³⁾
SN74LVC1G132	DBV (SOT-23, 5)	2.9mm × 2.8mm	2.9mm × 1.6mm
	DCK (SC70, 5)	2mm × 2.1mm	2mm × 1.25mm

- (1) For more information, see [Mechanical, Packaging, and Orderable Information](#).
- (2) The package size (length × width) is a nominal value and includes pins, where applicable.
- (3) The body size (length × width) is a nominal value and does not include pins.



Logic Diagram



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4 Pin Configuration and Functions

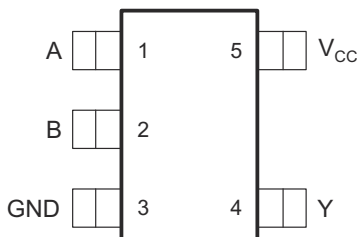
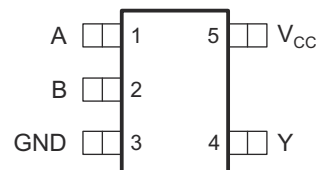


Figure 4-1. DBV Package 5-Pin SOT-23 Top View



See mechanical drawings for dimensions.

Figure 4-2. DCK Package 5-Pin SC70 Top View

Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	DBV, DCK		
A	1	I	A logic input
B	2	I	B logic input
GND	3	—	Ground
V _{CC}	5	—	Positive supply
Y	4	O	Y NAND logic output

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V _{CC}	Supply voltage		−0.5	6.5	V
V _I	Input voltage ⁽²⁾		−0.5	6.5	V
V _O	Voltage range applied to any output in the high-impedance or power-off state ⁽²⁾		−0.5	6.5	V
V _O	Voltage range applied to any output in the high or low state ^{(2) (3)}		−0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0	−50		mA
I _{OK}	Output clamp current	V _O < 0	−50		mA
I _O	Continuous output current		±50		mA
	Continuous current through V _{CC} or GND		±100		mA
T _{stg}	Storage temperature		−65	150	°C

- (1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
- (2) The input and output negative-voltage ratings can be exceeded if the input and output current ratings are observed.
- (3) The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

5.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	2000	V
	Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	1000	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V_{CC} ⁽¹⁾ Supply voltage	Operating	1.65	5.5	V
	Data retention only	1.5		
V_I Input voltage		0	5.5	V
V_O Output voltage		0	V_{CC}	V
I_{OH} High-level output current	$V_{CC} = 1.65V$		–4	mA
	$V_{CC} = 2.3V$		–8	
	$V_{CC} = 3V$		–16	
			–24	
	$V_{CC} = 4.5V$		–32	
I_{OL} Low-level output current	$V_{CC} = 1.65V$		4	mA
	$V_{CC} = 2.3V$		8	
	$V_{CC} = 3V$		16	
			24	
	$V_{CC} = 4.5V$		32	
T_A Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application note, [Implications of Slow or Floating CMOS Inputs](#).

5.4 Thermal Information

PACKAGE	PINS	THERMAL METRIC ⁽¹⁾						UNIT
		$R_{\theta JA}$	$R_{\theta JC(top)}$	$R_{\theta JB}$	Ψ_{JT}	Ψ_{JB}	$R_{\theta JC(bot)}$	
DBV (SOT-23)	5	357.1	263.7	264.4	195.6	262.2	–	°C/W
DCK (SOT-SC70)	5	371	297.5	258.6	195.6	256.2	–	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application note.

5.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V _{CC}	–40°C to +85°C			–40°C to +125°C			UNIT
				MIN	TYP ⁽¹⁾	MAX	MIN	TYP ⁽¹⁾	MAX	
V _{T+} Positive-going input threshold voltage		1.65V	0.79		1.16	0.79		1.16	V	
		2.3V	1.11		1.56	1.11		1.56		
		3V	1.5		1.87	1.5		1.87		
		4.5V	2.16		2.74	2.16		2.74		
		5.5V	2.61		3.33	2.61		3.33		
V _{T–} Negative-going input threshold voltage		1.65V	0.39		0.62	0.39		0.62	V	
		2.3V	0.58		0.87	0.58		0.87		
		3V	0.84		1.14	0.84		1.16		
		4.5V	1.41		1.79	1.41		1.84		
		5.5V	1.87		2.29	1.87		2.33		
ΔV _T Hysteresis (V _{T+} – V _{T–})		1.65V	0.37		0.62	0.37		0.62	V	
		2.3V	0.48		0.77	0.48		0.77		
		3V	0.56		0.87	0.54		0.87		
		4.5V	0.71		1.04	0.66		1.04		
		5.5V	0.71		1.11	0.67		1.11		
V _{OH}	I _{OH} = –100 μA	1.65V to 5.5V	V _{CC} – 0.1			V _{CC} – 0.1			V	
	I _{OH} = –4mA	1.65V	1.2			1.2				
	I _{OH} = –8mA	2.3V	1.9			1.9				
	I _{OH} = –16mA	3V	2.4			2.4				
	I _{OH} = –24mA		2.3			2.3				
	I _{OH} = –32mA	4.5V	3.8			3.8				
V _{OL}	I _{OL} = 100 μA	1.65V to 5.5V	0.1			0.1			V	
	I _{OL} = 4mA	1.65V	0.45			0.45				
	I _{OL} = 8mA	2.3V	0.3			0.3				
	I _{OL} = 16mA	3V	0.4			0.4				
	I _{OL} = 24mA		0.55			0.55				
	I _{OL} = 32mA	4.5V	0.55			0.55				
I _I	A or B inputs	V _I = 5.5V or GND	1.65V to 5.5V	±1			±1			μA
I _{off}		V _I or V _O = 5.5V	0	±10			±10			μA
I _{CC}		V _I = V _{CC} or GND, I _O = 0	1.65V to 5.5V	10			10			μA
ΔI _{CC}		One input at V _{CC} – 0.6V, Other inputs at V _{CC} or GND	3V to 5.5V	500			500			μA
C _i		V _I = V _{CC} or GND	3.3V	3.5						pF

(1) All typical values are at V_{CC} = 3.3V, T_A = 25°C.

5.6 Switching Characteristics: –40°C to +85°C, $C_L = 15\text{pF}$

over recommended operating free-air temperature range, $C_L = 15\text{pF}$ (unless otherwise noted) (see [Figure 6-1](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to +85°C								UNIT
			V _{CC} = 1.8V ±0.15V		V _{CC} = 2.5V ±0.2V		V _{CC} = 3.3V ±0.3V		V _{CC} = 5V ±0.5V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	4	16	2.5	7	2	5.3	1.5	4.4	ns

5.7 Switching Characteristics: –40°C to +85°C

over recommended operating free-air temperature range, $C_L = 30\text{pF}$ or 50pF (unless otherwise noted) (see [Figure 6-2](#))

PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to +85°C								UNIT
			V _{CC} = 1.8V ±0.15V		V _{CC} = 2.5V ±0.2V		V _{CC} = 3.3V ±0.3V		V _{CC} = 5V ±0.5V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	4	16	3	7.5	2	6	2	5	ns

5.8 Switching Characteristics: –40°C to +125°C

over recommended operating free-air temperature range, $C_L = 30\text{pF}$ or 50pF (unless otherwise noted) (see [Figure 6-2](#))

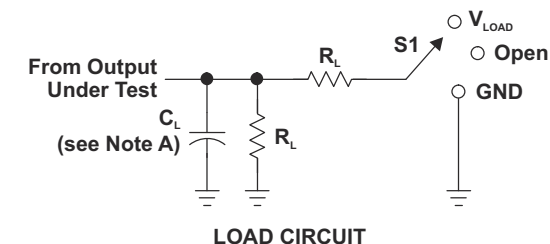
PARAMETER	FROM (INPUT)	TO (OUTPUT)	–40°C to +125°C								UNIT
			V _{CC} = 1.8V ±0.15V		V _{CC} = 2.5V ±0.2V		V _{CC} = 3.3V ±0.3V		V _{CC} = 5V ±0.5V		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Y	4	16.5	3	8	2	6.5	2	5.5	ns

5.9 Operating Characteristics

$T_A = 25^\circ\text{C}$

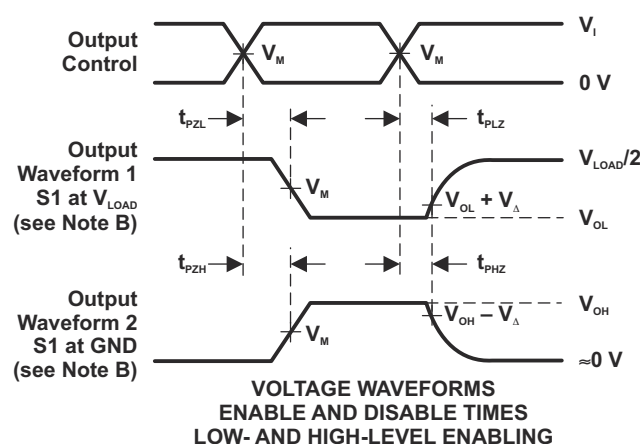
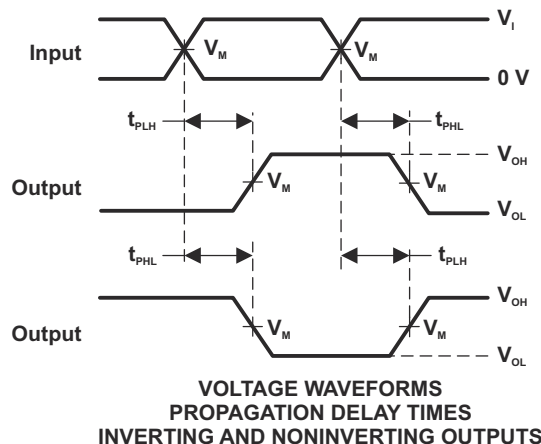
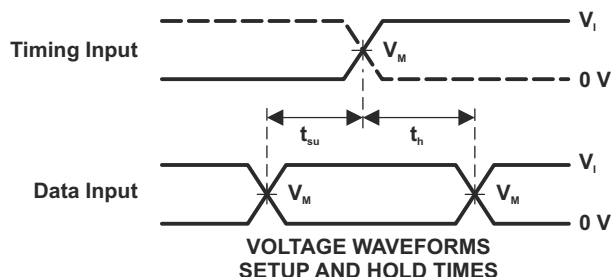
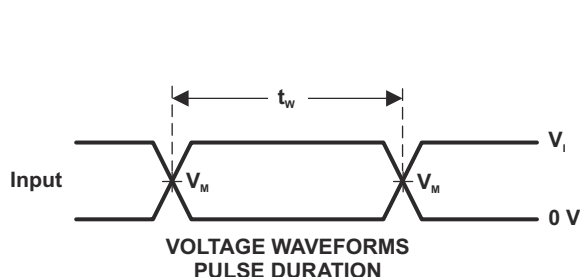
PARAMETER		TEST CONDITIONS	$V_{CC} = 1.8\text{V}$	$V_{CC} = 2.5\text{V}$	$V_{CC} = 3.3\text{V}$	$V_{CC} = 5\text{V}$	UNIT
			TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	$f = 10\text{MHz}$	17	18	18	20	pF

6 Parameter Measurement Information



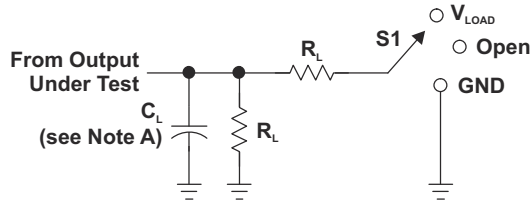
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	15 pF	1 M Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	15 pF	1 M Ω	0.3 V



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10\text{ MHz}$, $Z_o = 50\ \Omega$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{on} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

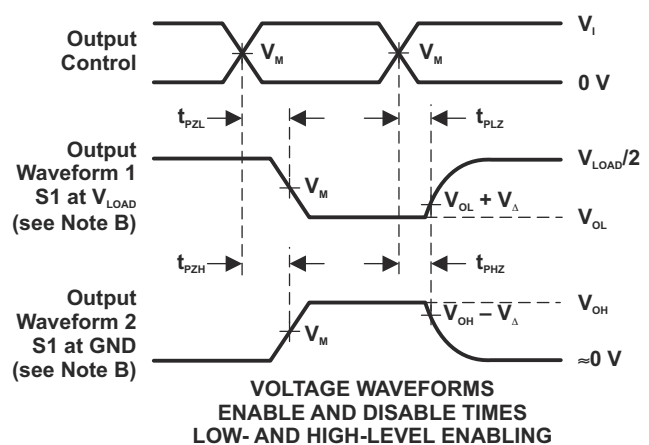
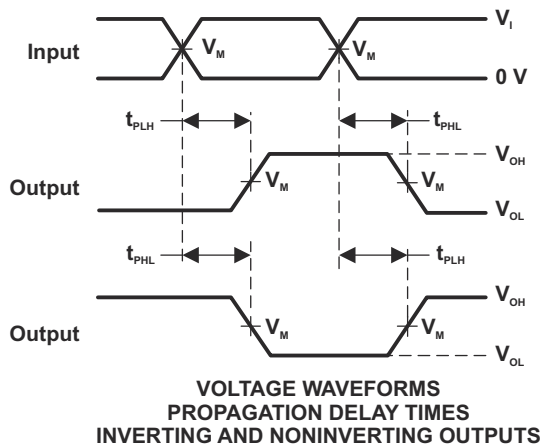
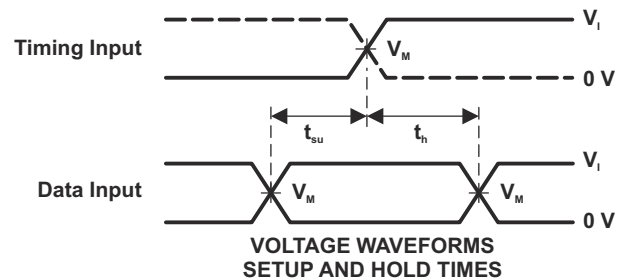
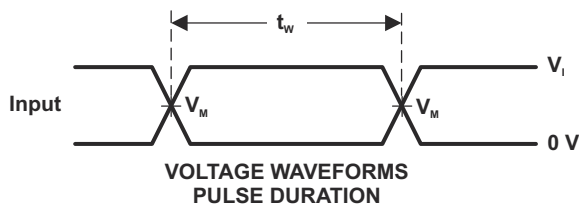
Figure 6-1. Load Circuit and Voltage Waveforms



LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_{Δ}
	V_I	t_r/t_f					
$1.8\text{ V} \pm 0.15\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	1 k Ω	0.15 V
$2.5\text{ V} \pm 0.2\text{ V}$	V_{CC}	$\leq 2\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3\text{ V} \pm 0.3\text{ V}$	3 V	$\leq 2.5\text{ ns}$	1.5 V	6 V	50 pF	500 Ω	0.3 V
$5\text{ V} \pm 0.5\text{ V}$	V_{CC}	$\leq 2.5\text{ ns}$	$V_{CC}/2$	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V



- NOTES:
- A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR $\leq 10\text{ MHz}$, $Z_o = 50\ \Omega$.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

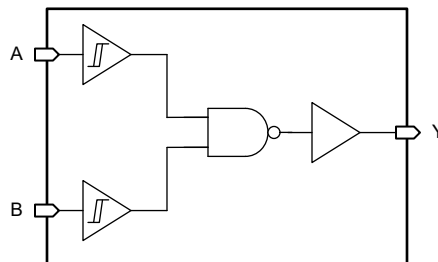
Figure 6-2. Load Circuit and Voltage Waveforms

7 Detailed Description

7.1 Overview

This device is a 2-input NAND Gate with Schmitt-trigger inputs which performs the Boolean function $Y = \overline{A \bullet B}$ in positive logic.

7.2 Functional Block Diagram



Logic Diagram (Positive Logic)

7.3 Feature Description

7.3.1 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device can create fast edges into light loads, so routing and load conditions must be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. Limit the output power of the device to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs must be left disconnected.

7.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, properly terminating unused inputs is still recommended. Driving the inputs with slow transitioning signals increases dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see [Understanding Schmitt Triggers](#).

7.3.3 Partial Power Down (I_{off})

This device includes circuitry to disable all outputs when the supply pin is held at 0V. When disabled, the outputs neither source nor sink current, regardless of the input voltages. The amount of leakage current at each output is defined by the I_{off} specification in the *Electrical Characteristics* table.

7.3.4 Clamp Diode Structure

Figure 7-1 shows the inputs and outputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

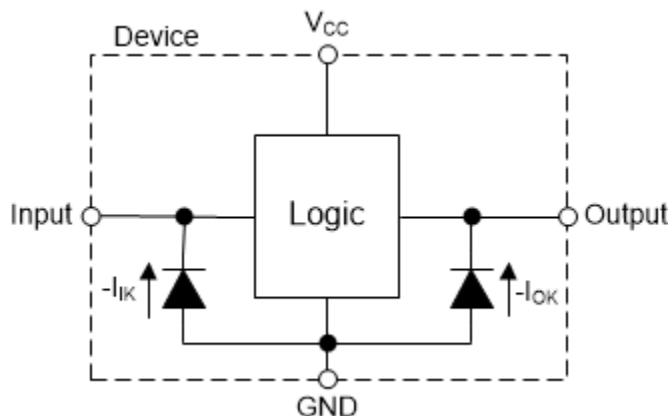


Figure 7-1. Electrical Placement of Clamping Diodes for Each Input and Output

7.3.5 Over-Voltage Tolerant Inputs

The SN74LVC1G132 includes over-voltage tolerant inputs. The input pins support high-state input voltages larger than the supply voltage by utilizing an input protection circuit that does not include a standard positive clamp diode. See *Recommended Operating Conditions* for the recommended input voltage.

CAUTION

Do not exceed the maximum input voltage range provided in *Absolute Maximum Ratings*. Exceeding the maximum input voltage range rating can cause immediate and permanent damage to the device.

7.4 Device Functional Modes

Table 7-1. Function Table

INPUTS		OUTPUT
A	B	Y
H	H	L
L	X	H
X	L	H

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

In this application, two 2-input NAND gates are used to create an active-low SR latch as shown in [Figure 8-1](#). The two additional gates can be used for a second SR latch, or the inputs can be grounded and both channels left unused.

The SN74LVC1G132 is used to drive the tamper indicator LED and provide one bit of data to the system controller. When the tamper switch outputs LOW, the output Q becomes HIGH. This output remains HIGH until the system controller addresses the event and sends a LOW signal to the R input which returns the Q output back to LOW.

8.2 Typical Application

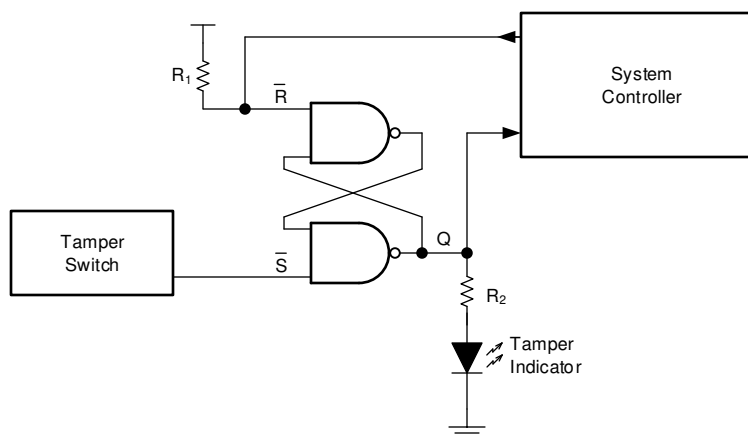


Figure 8-1. Typical application block diagram

8.2.1 Design Requirements

8.2.1.1 Power Considerations

Verify that the desired supply voltage is within the range specified in the *Electrical Characteristics*. The supply voltage sets the device electrical characteristics, as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74LVC1G132 plus the maximum static supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Verify that the maximum total current through V_{CC} listed in the *Absolute Maximum Ratings* is not exceeded.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74LVC1G132 plus the maximum supply current, I_{CC} , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into the ground connection. Verify that the maximum total current through GND listed in the *Absolute Maximum Ratings* is not exceeded.

The SN74LVC1G132 can drive a load with a total capacitance less than or equal to 50pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, TI recommends adding a series resistor between the output and capacitor to prevent excessive current.

The SN74LVC1G132 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OH} and V_{OL} . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in the [CMOS Power Consumption and Cpd Calculation application note](#).

Thermal increase can be calculated using the information provided in the [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#).

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

8.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. The unused inputs can be directly terminated if the input is completely unused, or the inputs can be connected with a pullup or pulldown resistor if the input is used sometimes, but not always. A pullup resistor is used for a default state of HIGH, and a pulldown resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74LVC1G132 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10kΩ resistor value is often used due to these factors.

The SN74LVC1G132 has no input signal transition rate requirements because the device has Schmitt-Trigger inputs.

Another benefit to having Schmitt-Trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value provides the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-Trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* for additional information regarding the inputs for this device.

8.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output decreases the output voltage as specified by the V_{OH} specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output increases the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Push-pull outputs that can be in opposite states, even for a very short time period, must never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to the *Feature Description* section for additional information regarding the outputs for this device.

8.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Verify that the capacitive load at the output is $\leq 50\text{pF}$. Low load capacitance can be accomplished by providing short, appropriately sized traces from the SN74LVC1G132 to the receiving device.
3. Verify that the resistive load at the output is larger than $(V_{CC} / I_{O(max)})\Omega$. Never violate the maximum output current from the *Absolute Maximum Ratings*. Most CMOS inputs have a resistive load measured in $M\Omega$; much larger than the minimum calculated previously.
4. Thermal issues are rarely a concern for logic gates; however, the power consumption and thermal increase can be calculated using the steps provided in the [CMOS Power Consumption and Cpd Calculation application note](#).

8.2.3 Application Curves

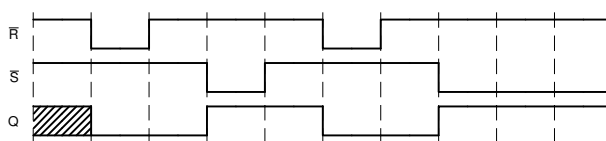


Figure 8-2. Application timing diagram

8.3 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating listed in the *Recommended Operating Conditions*.

Verify that each V_{CC} terminal has a good bypass capacitor to prevent power disturbance. For the SN74LVC1G132, a $0.1\mu\text{F}$ bypass capacitor is recommended. To reject different frequencies of noise, use multiple bypass capacitors in parallel. Capacitors with values of $0.1\mu\text{F}$ and $1\mu\text{F}$ are commonly used in parallel.

8.4 Layout

8.4.1 Layout Guidelines

- Bypass capacitor placement
 - Place near the positive supply terminal of the device
 - Provide an electrically short ground return path
 - Use wide traces to minimize impedance
 - Keep the device, capacitors, and traces on the same side of the board whenever possible
- Signal trace geometry
 - 8mil to 12mil trace width
 - Lengths less than 12cm to minimize transmission line effects
 - Avoid 90° corners for signal traces
 - Use an unbroken ground plane below signal traces
 - Flood fill areas around signal traces with ground
 - Parallel traces must be separated by at least 3x dielectric thickness
 - For traces longer than 12cm
 - Use impedance controlled traces
 - Source-terminate using a series damping resistor near the output
 - Avoid branches; buffer each signal that must branch separately

8.4.2 Layout Example

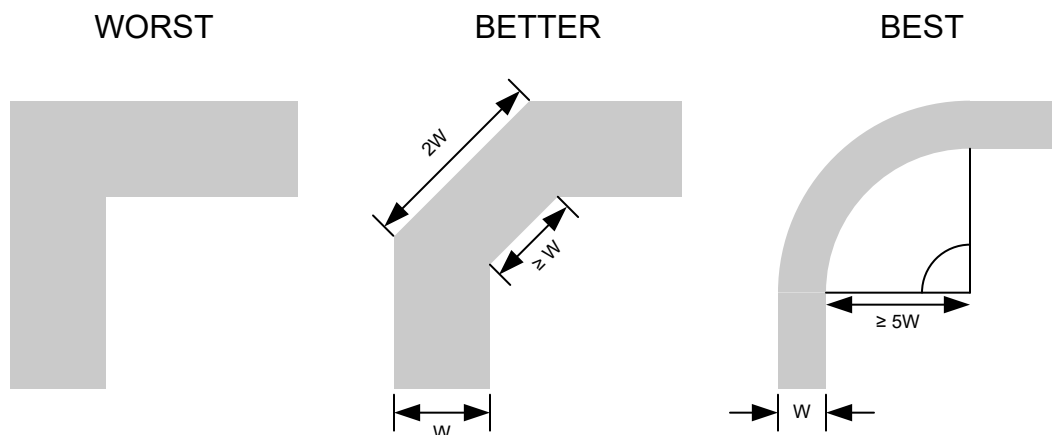


Figure 8-3. Example Trace Corners for Improved Signal Integrity

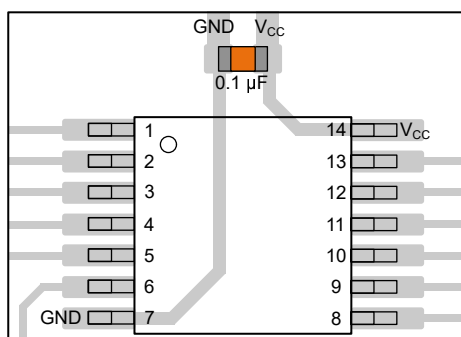


Figure 8-4. Example Bypass Capacitor Placement for TSSOP and Similar Packages

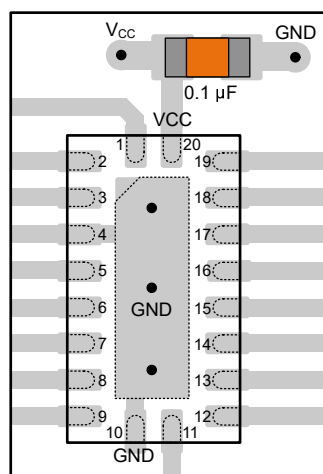


Figure 8-5. Example Bypass Capacitor Placement for WQFN and Similar Packages

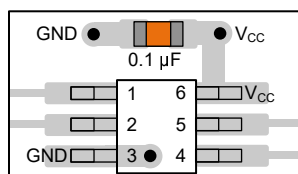


Figure 8-6. Example Bypass Capacitor Placement for SOT, SC70 and Similar Packages

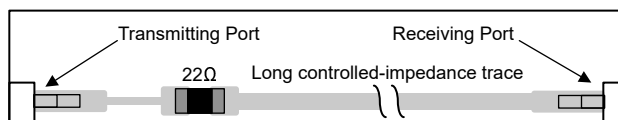


Figure 8-7. Example Damping Resistor Placement for Improved Signal Integrity

9 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and \$C_{pd}\$ Calculation application note](#)
- Texas Instruments, [Designing With Logic application note](#)
- Texas Instruments, [Thermal Characteristics of Standard Linear and Logic \(SLL\) Packages and Devices application note](#)

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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9.4 Trademarks

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9.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from April 1, 2014 to August 12, 2026 (from Revision D (June 2017) to Revision E (August 2026))

	Page
• Updated <i>Device Information</i> table to include body and package dimensions.....	1
• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Updated format for <i>Thermal Information</i> table.....	5
• Extended <i>Thermal Information</i> table to include $R_{\theta JC(top)}$, $R_{\theta JB}$, Ψ_{JT} , Ψ_{JB} , $R_{\theta JC(bot)}$	5
• Changed Junction-to-ambient thermal resistance value for DBV package from: 206°C/W to: 357.1°C/W.....	5
• Changed Junction-to-ambient thermal resistance value for DCK package from: 252°C/W to: 371°C/W.....	5
• Updated <i>Overview</i> , <i>Application and Implementation</i> , <i>Device and Documentation Support</i> sections to extend detailed feature descriptions and more detailed information.	9

-
- Added parallel trace spacing recommendation to layout guidelines. Changed wording of "Avoid branches; buffer signals that must branch separately" to "Avoid branches; buffer each signal that must branch separately" 14
-

Changes from Revision C (December 2013) to Revision D (June 2017)	Page
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- | | |
|---|--------|
| <ul style="list-style-type: none"> • Added <i>Applications</i>, <i>Device Information</i> table, <i>Pin Configuration and Functions</i> section, <i>ESD Ratings</i> table, <i>Thermal Information</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i>, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section..... • Deleted YEP, YZP packages throughout data sheet..... | 1
1 |
|---|--------|
-

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
74LVC1G132DBVRG4.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C3BR
74LVC1G132DCKRG4	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D5R
74LVC1G132DCKRG4.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D5R
74LVC1G132DCKTG4	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D5R
74LVC1G132DCKTG4.B	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	D5R
SN74LVC1G132DBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C3BJ, C3BR)
SN74LVC1G132DBVR.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C3BJ, C3BR)
SN74LVC1G132DBVR.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C3BJ, C3BR)
SN74LVC1G132DBVT	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C3BJ, C3BR)
SN74LVC1G132DBVT.B	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(C3BJ, C3BR)
SN74LVC1G132DBVTG4.B	Active	Production	SOT-23 (DBV) 5	250 SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C3BR
SN74LVC1G132DCKR	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(D55, D5J, D5R)
SN74LVC1G132DCKR.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(D55, D5J, D5R)
SN74LVC1G132DCKR.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(D55, D5J, D5R)
SN74LVC1G132DCKRG4.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
SN74LVC1G132DCKRG4.B	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
SN74LVC1G132DCKT	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(D55, D5J, D5R)
SN74LVC1G132DCKT.B	Active	Production	SC70 (DCK) 5	250 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	(D55, D5J, D5R)

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION

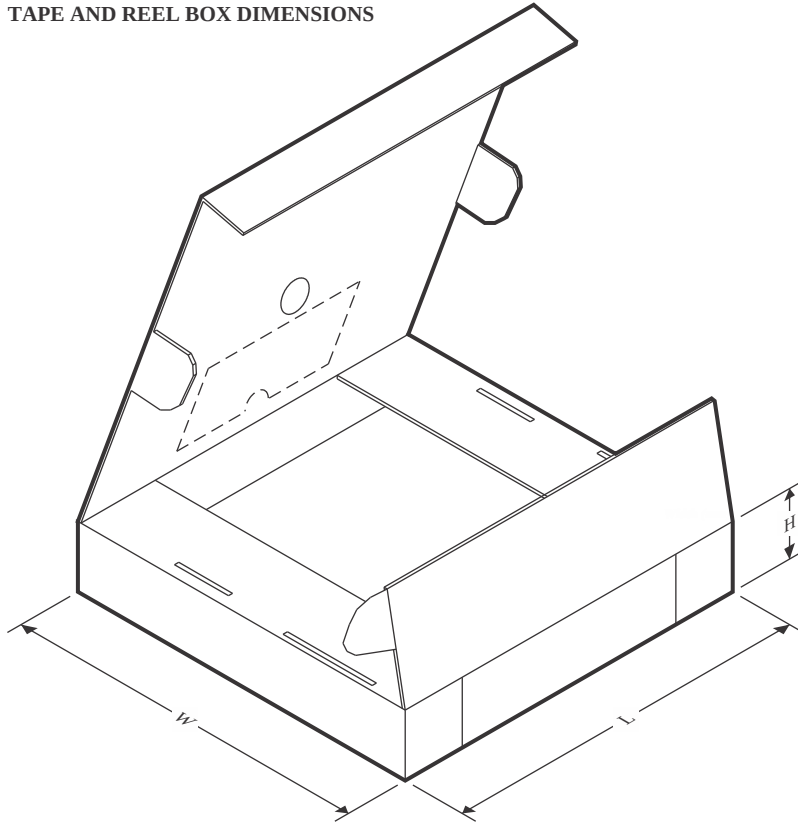


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
74LVC1G132DCKRG4	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
74LVC1G132DCKTG4	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G132DBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DBVT	SOT-23	DBV	5	250	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
SN74LVC1G132DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G132DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G132DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G132DCKR	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3
SN74LVC1G132DCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.55	1.2	4.0	8.0	Q3

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G132DCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G132DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
74LVC1G132DCKRG4	SC70	DCK	5	3000	183.0	183.0	20.0
74LVC1G132DCKTG4	SC70	DCK	5	250	183.0	183.0	20.0
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	208.0	191.0	35.0
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74LVC1G132DBVR	SOT-23	DBV	5	3000	210.0	185.0	35.0
SN74LVC1G132DBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
SN74LVC1G132DBVT	SOT-23	DBV	5	250	202.0	201.0	28.0
SN74LVC1G132DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G132DBVT	SOT-23	DBV	5	250	210.0	185.0	35.0
SN74LVC1G132DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G132DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74LVC1G132DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G132DCKR	SC70	DCK	5	3000	208.0	191.0	35.0
SN74LVC1G132DCKR	SC70	DCK	5	3000	210.0	185.0	35.0
SN74LVC1G132DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G132DCKT	SC70	DCK	5	250	202.0	201.0	28.0



SOT - 1.1 max height

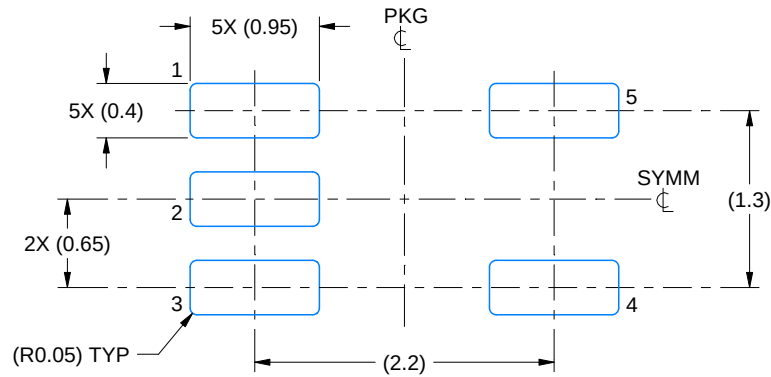
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

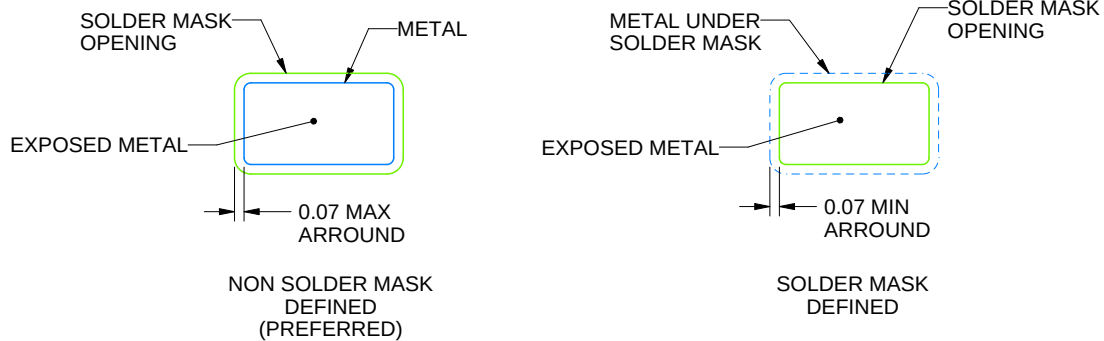
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

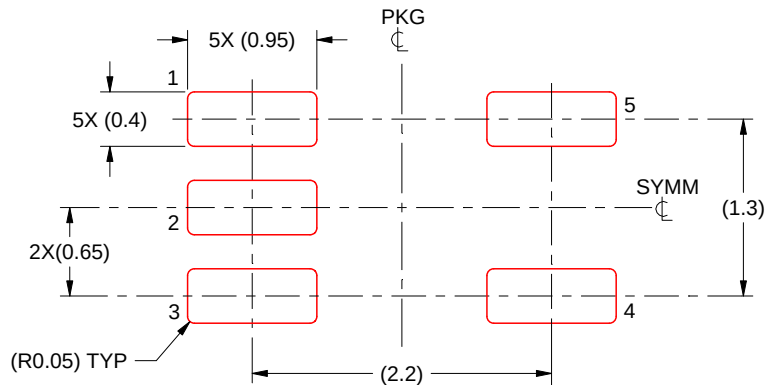


SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

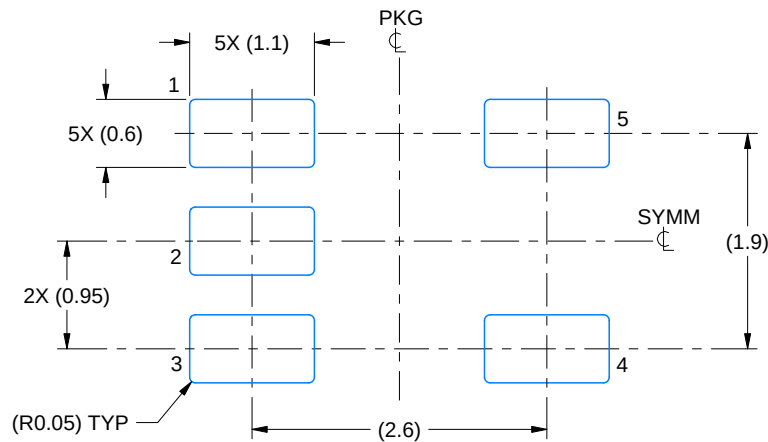
9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

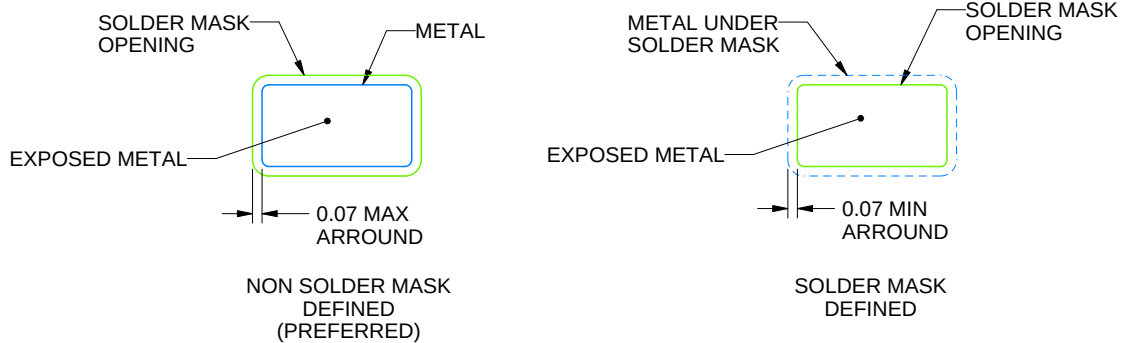
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

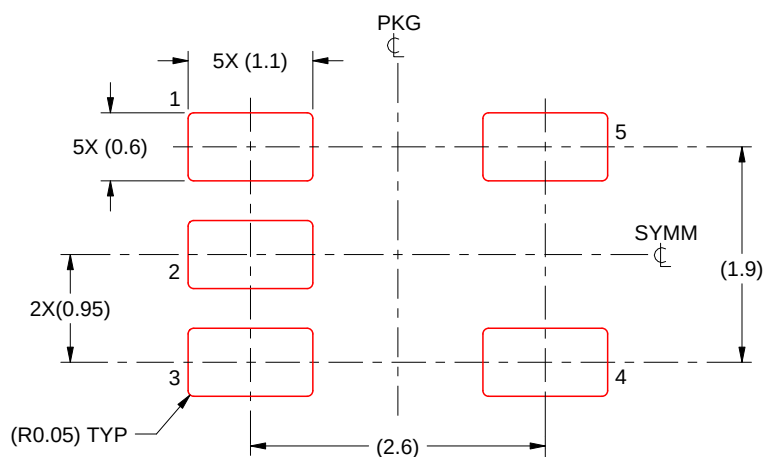
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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